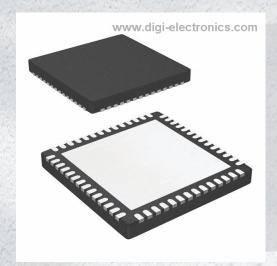


PI6LC48S25BZBBIEX Datasheet



https://www.DiGi-Electronics.com

DiGi Electronics Part Number PI6LC48S25BZBBIEX-DG

Manufacturer Diodes Incorporated

Manufacturer Product Number PI6LC48S25BZBBIEX

Description IC CLOCK GENERATOR 56TQFN

Detailed Description Clock Generator IC 312.5MHz 1 56-VFQFN Exposed

Pad



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.



Purchase and inquiry

Manufacturer Draduct Number	Manufacturer
Manufacturer Product Number:	Manufacturer:
PI6LC48S25BZBBIEX	Diodes Incorporated
Series:	Product Status:
HiFlex™	Active
DiGi-Electronics Programmable:	Type:
Not Verified	Clock Generator
PLL:	Input:
Yes with Bypass	CMOS, Crystal
Output:	Number of Circuits:
LVDS, LVPECL	1
Ratio - Input:Output:	Differential - Input:Output:
3:11	Yes/Yes
Frequency - Max:	Divider/Multiplier:
312.5MHz	Yes/No
Voltage - Supply:	Operating Temperature:
2.375V ~ 3.63V	-40°C ~ 85°C (TA)
Mounting Type:	Package / Case:
Surface Mount	56-VFQFN Exposed Pad
Supplier Device Package:	Base Product Number:
56-TQFN (8x8)	PI6LC48

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	

8542.39.0001



Next Generation HiFlexTM Ethernet Network Clock Generator

Features

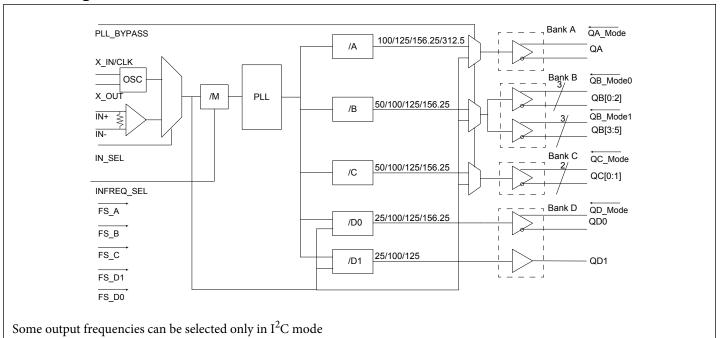
- → 3.3V & 2.5V supply voltage
- → Crystal/CMOS input: 25 MHz
- → Differential input: 25MHz, 125MHz, and 156.25 MHz
- → Output frequencies: 312.5, 156.25, 125, 100, 50, 25MHz
- → 4 Output banks with selectable output signaling: LVPECL or LVDS
- → Low 0.3ps typical integrated phase noise design: 156.25MHz (12kHz to 20MHz)
- → PLL Bypass mode for test
- → Power supply noise rejection: -52 dBc typical @ VDD
- → Packaging (Pb-free & Green): 56-lead 8×8mm TQFN
- → Industrial temperature support: -40C to 85C

Description

The PI6LC48S25B is an LC VCO based low phase noise design intended for 10GbE applications. Typical 10GbE usage assumes a 25MHz crystal input, while the PLL loop is used to generate the 156.25MHz and other Ethernet clock frequencies. An additional buffered crystal oscillator output is provided to serve as a low noise reference for other circuitry.

For Ethernet applications other than 10GbE, programmable dividers allow for simultaneous output of 312.5, 156.25, 125, 100, 50, and 25MHz. This device offers both pin selection and I^2C interface to give more options to meet various system needs.

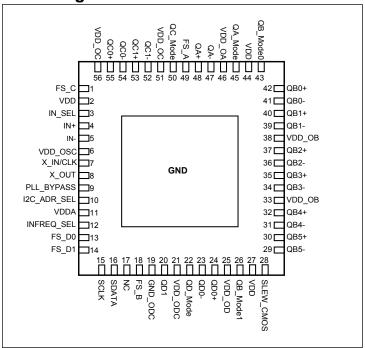
Block Diagram







Pin Configuration



Pin Description

Pin #	Pin Name	Туре		Description
1	FS_C	Input	Tri-level	Output frequency select for Bank C output
2, 27, 44	VDD	Power	-	Core supply
3	IN_SEL	Input	CMOS	Input select between Xtal and differential input
4	IN+	Input	LVPECL	Differential reference input, also accepts AC-coupled LVDS, CML, HCSL or
5	IN-	Input	LVPECL	LVPECL. Differential inputs have an internal 100Ω cross resistor.
6	VDD_OSC	Power	-	Power supply for Xtal Oscillator circuit
7	X_IN/CLK	Input		Xtal or clock input, connect to a 25MHz Xtal or single-ended clock
8	X_OUT	Output		Xtal output
9	PLL_BYPASS	Input	CMOS	PLL bypass, provide input frequency to Bank A, BankB, and Bank C
10	I2C_ADR_SEL	Input	CMOS	I2C address selection.
11	VDDA	Power	-	Analog supply
12	INFREQ_SEL	Input	Tri-level	Input frequency selection for reference input
13	FS_D0	Input	Tri-level	Output frequency select for Bank D differential output
14	FS_D1	Input	Tri-level	Output frequency select for Bank D CMOS output
15	SCLK	Input		I ² C clock input
16	SDATA	Input/ Output		I ² C Data line





Pin Description Cont.

Pin #	Pin Name Type		pe	Description	
17	NC			Reserved pin. Do not connect this pin	
18	FS_B	Input	Tri-level	Output frequency select for Bank B	
19	GND_ODC	Power		Ground for bank D CMOS output	
20	QD1	Output	CMOS	Bank D output 1	
21	VDD_ODC	Power		Power supply for bank D CMOS output	
22	QD_Mode	Input	Tri-level	Bank D differential output control	
23, 24	QD0-, QD0+	Output	LVPECL/ LVDS	Bank D differential output	
25	VDD_OD	Power		Power supply for bank D differential outputs	
26	QB_Mode1	Input	Tri-level	Bank B QB3 ~ QB5 differential output control	
28	SLEW_CMOS	Input	CMOS	Output slew rate control for the CMOS output	
29, 30	QB5-, QB5+	Output	LVPECL/ LVDS	Bank B differential output	
31, 32	QB4-, QB4+	Output	LVPECL/ LVDS	Bank B differential output	
33, 38	VDD_OB	Power		Power supply for bank B differential outputs	
34, 35	QB3-, QB3+	Output	LVPECL/ LVDS	Bank B differential output	
36, 37	QB2-, QB2+	Output	LVPECL/ LVDS	Bank B differential output	
39, 40	QB1-, QB1+	Output	LVPECL/ LVDS	Bank B differential output	
41, 42	QB0-, QB0+	Output	LVPECL/ LVDS	Bank B differential output	
43	QB_Mode0	Input	Tri-level	Bank B QB0 ~ QB2 differential output control	
45	QA_Mode	Input	Tri-level	Bank A differential output control	
46	VDD_OA	Power		Power supply for bank A differential outputs	
47, 48	QA-, QA+	Output	LVPECL/ LVDS	Bank A differential output	
49	FS_A	Input	Tri-level	Output frequency select for Bank A	
50	QC_Mode	Input	Tri-level	Bank C differential output control	
51, 56	VDD_OC	Power		Power supply for bank A differential outputs	
52, 53	QC1-, QC1+	Output	LVPECL/ LVDS	Bank C differential output	
54, 55	QC0-, QC0+	Output	LVPECL/ LVDS	Bank C differential output	
E-pad	GND	Power		Connect to ground, use thermal vias	





Input MUX Selection

IN_SEL	Input Source	
0	Crystal Input (X_IN/CLK, X_OUT)	
1	Differential Input (IN+, IN-)	
NC	Crystal Input (X_IN/CLK, X_OUT)	

Reference Input Frequency Select Table

INFREQ_SEL	Reference Input
0	25MHz
1	125MHz
NC	156.25MHz

PLL Bypass Control Function

PLL_BYPASS	PLL operation
0	PLL enabled
1	PLL bypassed

Bank A/B/C/D Differential Output Control

QA_ Mode	QA	QB_ Mode0	QB[2:0]	QB_ Mode1	QB[5:3]	QC_ Mode	QC[1:0]	QD_ Mode	QD0
0	LVPECL	0	LVPECL	0	LVPECL	0	LVPECL	0	LVPECL
1	LVDS	1	LVDS	1	LVDS	1	LVDS	1	LVDS
NC	Hi-Z	NC	Hi-Z	NC	Hi-Z	NC	Hi-Z	NC	Hi-Z

Bank A/B/C Output Frequency Control Table

FS_A	Bank A Output Freq.	FS_B	Bank B Output Freq.	FS_C	Bank C Output Freq.
0	156.25MHz	0	156.25MHz	0	156.25MHz
1	125MHz	1	125MHz	1	125MHz
NC	312.5MHz	NC	50MHz	NC	100MHz

Bank D Output Frequency Control Table

FS_D0	Bank D Diff. Output Freq.	FS_D1	Bank D CMOS Output Freq.
0	156.25MHz	0	Hi-Z
1	125MHz	1	125MHz
NC	f_{IN}	NC	f_{IN}

Output Slew Rate Control Table

SLEW_CMOS	Output Slew rate
0	Normal mode
1	Slow mode

I2C Address Selection Table

I ² C_ADR_SEL	I2C Address
0	DC (h)
1	DE (h)





Maximum Ratings

(Above which useful life may be impaired. For user guidelines, not tested.)

Note: Stresses greater than those listed under MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Operating Conditions

Symbol	Parameters	Conditions	Min.	Тур.	Max.	Units
V	Come Devices Comply Voltage		2.97	3.3	3.63	V
V_{DD}	Core Power Supply Voltage		2.375	2.5	2.625	V
17	Outmut Davier Cumply Valtage		2.97	3.3	3.63	V
V_{DD_OX}	Output Power Supply Voltage		2.375	2.5	2.625	V
7.7	A la Daniera Comunica Valta		2.97	3.3	3.63	V
V_{DDA}	Analog Power Supply Voltage		2.375	2.5	2.625	V
I_{DD}	Power Supply Current				50	mA
T	Davies Comply Consent for Outputs	All outputs loaded, Diff. outputs are LVPECL			525	mA
I_{DD_O}	Power Supply Current for Outputs	All outputs loaded, Diff. outputs are LVDS			242	mA
I _{DDA}	Analog Power Supply Current				45	mA
T_{A}	Ambient Temperature		-40		85	°C

Input Electrical Characteristics

Symbol	Parameters	Conditions	Min.	Тур.	Max.	Units
R _{pu}	Internal pull up resistance			51		ΚΩ
R _{dn}	Internal pull down resistance			51		ΚΩ
C_{XTAL}	Internal capacitance on X_IN and X_OUT pins			12		pF





LVCMOS DC Electrical Characteristics

Symbol	Parameters	Conditions	Min.	Typ.	Max.	Units
37	T TT' 1 X7 16	$V_{\rm DD} = 3.3 V \pm 10\%$	2		V _{DD} +0.3	V
V_{IH}	Input High Voltage	$V_{\rm DD} = 2.5 V \pm 5\%$	1.7		V _{DD} +0.3	V
37	I	$V_{\rm DD} = 3.3 V \pm 10\%$	-0.3		0.8	V
$V_{\rm IL}$		$V_{\rm DD} = 2.5 V \pm 5\%$	-0.3		0.5	V
I _{IH}	Input High Current	$V_{IN} = V_{DD max}$.			150	μА
I _{IL}	Input Low Current	$V_{IN} = 0V$	-150			μΑ
		$V_{DD} = V_{DD_ODC} = 3.3V \pm 10\%;$	2.6			3.7
37	Output High Voltage	$I_{OH} = -12mA$	2.6			V
V _{OH}		$V_{DD} = V_{DD_ODC} = 2.5V \pm 5\%;$	1.0			V
		$I_{OH} = -8mA$	1.8			V
		$V_{DD} = V_{DD_ODC} = 3.3V \pm 10\%;$			0.5	V
3.7	Octobrill and Walter	$I_{OH} = 12mA$			0.5	V
V_{OL}	Output Low Voltage	$V_{DD} = V_{DD_ODC} = 2.5V \pm 5\%;$			0.5	V
		$I_{OH} = 8mA$			0.5	V
T_{DC}	Input Duty Cycle		35		65	%
D	CMOCO + +: 1	V _{DD_ODC} =3.3V		24		0
R _{OUT}	CMOS Output impedance	$V_{\rm DD_ODC}$ =2.5V		30		Ω
C _{IN}	Input Capacitance			3.5		pF

Differential Input DC Characteristics

Symbol	Parameters	Conditions	Min	Тур.	Max.	Units
V_{IH}	Input High Voltage				V _{DD} - 0.7	V
$V_{\rm IL}$	Input Low Voltage		V _{DD} - 2.0			V
V_{CM}	Input Bias Voltage		0.5		V _{DD} - 0.85	V
R _{IN}	Input Differential Impedance ¹		80	100	120	Ω
V _{IN-PP}	Input Differential Swing	Differential peak to peak	0.3		2.6	V

Note: 1. Differential input can be AC or DC coupled.

Crystal Characteristic

Parameters	Description	Min.	Тур	Max.	Units
OSCmode	Mode of Oscillation		Fundamenta	1	
FREQ	Frequency	10	25	40	MHz
ESR ¹	Equivalent Series Resistance			50	Ω
Cload	Load Capacitance		18		pF
Cshunt	Shunt Capacitance			7	pF
	Drive Level			250	uW

 $\textbf{Note: 1.} \ ESR \ value \ is \ dependent \ upon \ frequency \ of \ oscillation$





LVPECL Output DC Characteristics (1)

Symbol	Parameters	Condition	Min.	Тур.	Max.	Units
V _{OPP}	Output peak-peak Voltage	Single-ended		0.78		V
V _{OH}	Output High Voltage	Outputs terminated with 50Ω to	V _{DD_OX} - 1.4		V _{DD_OX} - 0.7	V
V _{OL}	Output Low Voltage	V _{DD_OX} - 2V	V _{DD_OX} - 2.0		V _{DD_OX} - 1.3	V

LVDS Output DC Characteristics (1)

Symbol	Parameters	Condition	Min.	Тур.	Max.	Units
V _{OPP}	Output Peak-peak Voltage	Single-ended	0.247		0.454	V
DV _{OPP}	V _{OPP} Magnitude Change				50	mV
Vos	Output Offset Voltage		1.125		1.375	V
DVOS	V _{OS} Magnitude Change				50	mV

AC Output Characteristics (see test configurations) ⁽¹⁾

 T_A =-40C to 85C; V_{DD} =3.3V±10%, V_{DD} O=3.3V±10%

Symbol	Parameters	Condition		Min.	Тур.	Max.	Units
		LVCMOS				125	MHz
f_{OUT}	Output Frequency	LVPECL				312.5	MHz
		LVDS				312.5	MHz
	Dia 1 F.11 Tim.	LUCMOS	Normal Mode ⁽²⁾	150	400	850	ps
t _{R/tF}	Rise and Fall Time; 20% ~80%	LVCMOS	Slow Mode ⁽³⁾			2.0	ns
	20% ~80%	LVPECL, LVDS			250	400	ps
		LVCMOS		45		55	%
t_{DC}	Duty Cycle	LVPECL, LVDS		48		52	%
		Bank A at 312.5	47		53	%	
	T	12kHz-20MHz @ 156.25MHz, 25MHz Xtal input			0.3	0.4	ps
tjphase	Integrated phase jitter (RMS)	10kHz-5MHz @ Xtal input	25MHz, 25MHz		0.33	0.4	ps
tj _{c-c}	Cycle to cycle jitter				28	30	ps
tj _{Pk-Pk}	Peak to Peak jitter				30	35	ps
			Offset 1kHz		-117		
		156.25MHz,	Offset 10kHz		-130		
f_N	Single-Side Band Phase Noise	25MHz Xtal	Offset 100kHz		-134		dBc/Hz
	110130	input	Offset 1MHz		-139		
			Offset 10MHz		-154		





AC Output Characteristics Cont.

 T_A =-40C to 85C; V_{DD} =3.3V±10%, V_{DD_O} =3.3V±10%

Symbol	Parameters	Condition	Min.	Тур.	Max.	Units
		V _{DD} , 50mVpp, 10k-1.5MHz		-52		
	Power Supply Noise Rejec-	V _{DDA} , 50mVpp, 10k-1.5MHz		-65		
PSNR	tion	V _{DD_Ox} , 50mVpp, 10k-1.5MHz		-50		dBc
t _{STARTUP}	Start time				10	ms
t _{LOCK}	PLL lock time				20	ms

Note:

- 1. V_{DD_O} = 3.3 is not valid with V_{DD} = 2.5V
- 2. Normal mode: All measurements are based on 20% to 80% of the single-ended waveform, Load is 4" trace and 4pF.
- 3. Slow mode: All measurements are based on 20% to 80% of the single-ended waveform, Load is 8" trace and 7pF.





Serial Data Interface (I²C compatible)

PI6LC48S25B is a slave only device that supports block read and block write protocol using a single 7-bit address and read/write bit as shown below.

Read and write block transfers can be stopped after any complete byte transfer.

For full electrical I2C compliance, it is recommended to use external pull-up resistors for SDATA and SCLK. The internal pull-up resistors have a size of $50k\Omega$ typical.

Address Assignment

A6	A5	A4	A3	A2	A1	A0	R/W
1	1	0	1	1	1	I ² C_ADR_SEL	1/0

How to Write

1 bit	7 bits	1 bit	1 bit	8 bits	1 bit	8 bits	1 bit	8 bits	1 bit	1 bit
Start bit	Address	W(0)	Ack	Data Byte	A alr	Data Byte	Ack	Data Byte	Ack	Stop bit
Start bit	Address	W(0)	ACK	(D)	Ack	(D+1)	ACK	 (D+N)	ACK	Stop bit

How to Read

1 bit	7 bits	1 bit	1 bit	8 bits	1 bit	8 bits	1 bit	8 bits	1 bit	1 bit
Start bit	Address	R(1)	Ack	Data Byte (D)	Ack	Data Byte (D+1)	Ack	 Data Byte (D+N)	Ack	Stop bit

Output Frequency I2C bit Control Table

FS_A (2-bit)	Bank A Freq.
0 0	156.25MHz
0 1	312.5MHz
1 0	125MHz
1 1	100MHz

FS_B (2-bit)	Bank B Freq.
0 0	156.25MHz
0 1	50MHz
1 0	125MHz
11	100MHz

FS_C (2-bit)	Bank C Freq.
0 0	156.25MHz
0 1	100MHz
1 0	125MHz
1 1	50MHz

FS_D0 (2-bit)	Diff Freq.
0 0	156.25MHz
0 1	f_{IN}
1 0	125MHz
1 1	100MHz

FS_D1 (2-bit)	CMOS Freq.			
0 0	Output disabled			
0 1	f_{IN}			
1 0	125MHz			
1 1	100MHz			





Input Frequency I2C bit Control Table

INFREQ_SEL (2-bit)	Input Freq.		
0 0	25MHz		
0 1	156.25MHz		
1 0	125MHz		
11	100MHz		

Byte 0: Output Frequency Selection Register

Bit	Control Function	Description	Туре	Power Up Condition	0	1
7	FS_C (1)	David Contract limits	RW	0	See FS_C I ² C co	
6	FS_C (0)	Bank C output divider	RW	0	See FS_C1 Cc	ontrol table
5	FS_B (1)	D 1 D 4 1 1 1	RW	0	2	
4	FS_B (0)	Bank B output divider	RW	0	See FS_B I ² C co	ntrol table
3	FS_A (1)	David A antique d'inidia	RW	0	See FS_A I ² C control table	
2	FS_A (0)	Bank A output divider	RW	0		
1	Vendor ID		RW	0		
0	Vendor ID		RW	0		

Byte 1: Output Frequency Selection and Misc. Register

Bit	Control Function	Description	Туре	Power Up Condition	0	1
7	I ² C pin control	Determine external pins or I ² C control mode	RW	0	External pins	I ² C
6	I2C_ADR_SEL	Select I ² C write address	RW	0	DC(h)	DE(h)
5	INFREQ_SEL (1)	T	RW	0	See INFREQ_SEL I ² C control	
4	INFREQ_SEL (0)	Input frequency selection	RW	0	table	
3	FS_D1 (1)	Parala D CMOS and and discillate	RW	1	See FS_D1 I ² C control table	
2	FS_D1 (0)	Bank D CMOS output divider	RW	1	See FS_DIT C	control table
1	FS_D0 (1)	Dank D. Diff autment dividen	RW	1	See FS_D0 I ² C	aontuol tabla
0	FS_D0 (0)	Bank D Diff. output divider	RW	1	see rs_D01 C	control table

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Byte 2: Output Enable Selection for Bank A and Bank B Register

Bit	Control Function	Description	Туре	Power Up Condition	0	1
7	Reserved					
6	OE for QB5	Output enable bit for QB5	RW	0	Enable	Disable
5	OE for QB4	Output enable bit for QB4	RW	0	Enable	Disable
4	OE for QB3	Output enable bit for QB3	RW	0	Enable	Disable
3	OE for QB2	Output enable bit for QB2	RW	0	Enable	Disable
2	OE for QB1	Output enable bit for QB1	RW	0	Enable	Disable
1	OE for QB0	Output enable bit for QB0	RW	0	Enable	Disable
0	OE for QA	Output enable bit for QA	RW	0	Enable	Disable

Byte 3: Output Enable and Output Type Selection for Bank C and D Register

Bit	Control Function	Description	Туре	Power Up Condition	0	1
7	Reserved					
6	QD0	Output Type Select QD Diff. output	RW	0	LVPECL	LVDS
5	QC1	Output Type Select QC1	RW	0	LVPECL	LVDS
4	QC0	Output Type Select QC0	RW	0	LVPECL	LVDS
3	OE for QD1	Output enable bit for QD1	RW	0	Enable	Disable
2	OE for QD0	Output enable bit for QD0	RW	0	Enable	Disable
1	OE for QC1	Output enable bit for QC1	RW	0	Enable	Disable
0	OE for QC0	Output enable bit for QC0	RW	0	Enable	Disable

Byte 4: Output Type Selection for Bank A and Bank B Register

Bit	Control Function	Description	Туре	Power Up Condition	0	1
7	Reserved					
6	QB5	Output Type Select QB5	RW	0	LVPECL	LVDS
5	QB4	Output Type Select QB4	RW	0	LVPECL	LVDS
4	QB3	Output Type Select QB3	RW	0	LVPECL	LVDS
3	QB2	Output Type Select QB2	RW	0	LVPECL	LVDS
2	QB1	Output Type Select QB1	RW	0	LVPECL	LVDS
1	QB0	Output Type Select QB0	RW	0	LVPECL	LVDS
0	QA	Output Type Select QA	RW	0	LVPECL	LVDS





Byte 5: Misc. Register

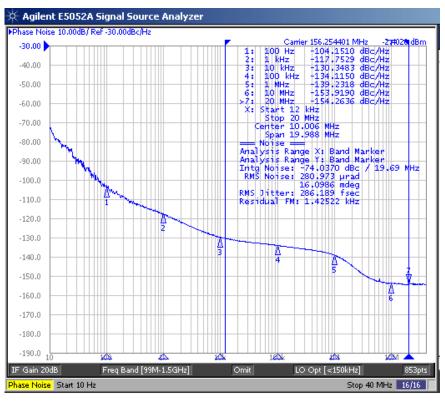
Bit	Control Function	Description	Туре	Power Up Condition	0	1
7	Reserved					
6	Reserved			0		
5	Reserved			0		
4	Reserved			0		
3	PLL_BYPASS	PLL bypass function	RW	0	PLL is enabled	PLL is by- passed
2	SLEW_CMOS	Output slew rate control for the CMOS output	RW	0	Normal mode	Slow mode
1	Reserved			0		
0	IN_SEL	Input selection	RW	0	Crystal	Reference

12

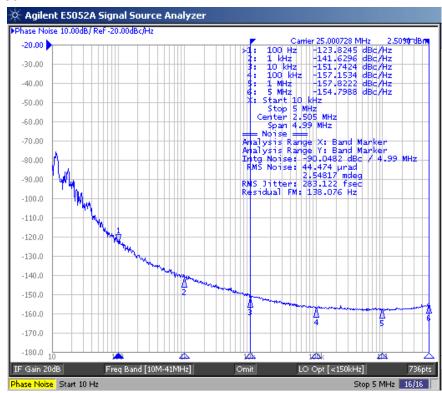




Phase Noise Plots 156.25MHz LVDS Clock



25MHz LVPECL Clock



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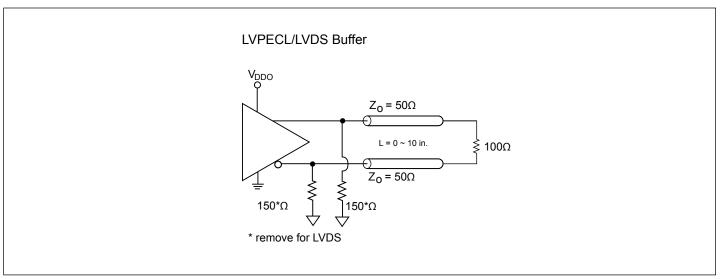


Figure 1. LVPECL and LVDS Test Circuit

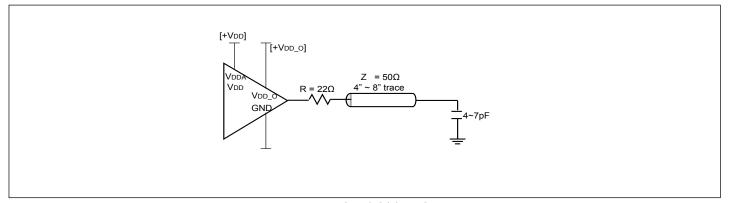


Figure 2. CMOS Test Circuit

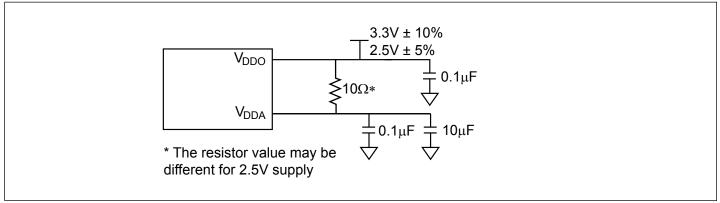


Figure 3. Power Supply Filter

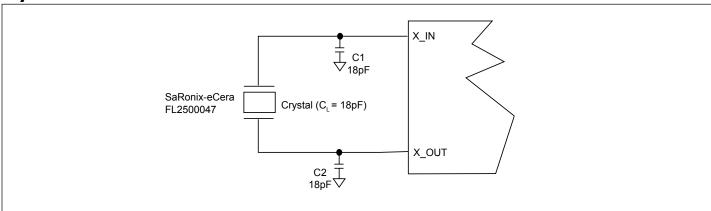




Crystal Circuit Connection

The following diagram shows PI6LC48S25B crystal circuit connection with a parallel crystal. For the CL=18pF crystal, it is suggested to use C1=18pF, C2=18pF. C1 and C2 can be adjusted to fine tune to the target ppm of crystal oscillator according to different board layouts.

Crystal Oscillator Circuit



Crystal Circuit Oscillator

Recommended Crystal Specification

Pericom recommends:

- a) FY2500081, SMD 5x3.2(4P), 25MHz, CL=18pF, +/-30ppm, http://www.pericom.com/pdf/datasheets/se/FY_F9.pdf
- b) FL2500047, SMD 3.2x2.5(4P), 25MHz, CL=18pF, +/-20ppm, http://www.pericom.com/pdf/datasheets/se/FL.pdf

Part Marking

ZBB Package



YY: Year

WW: Workweek

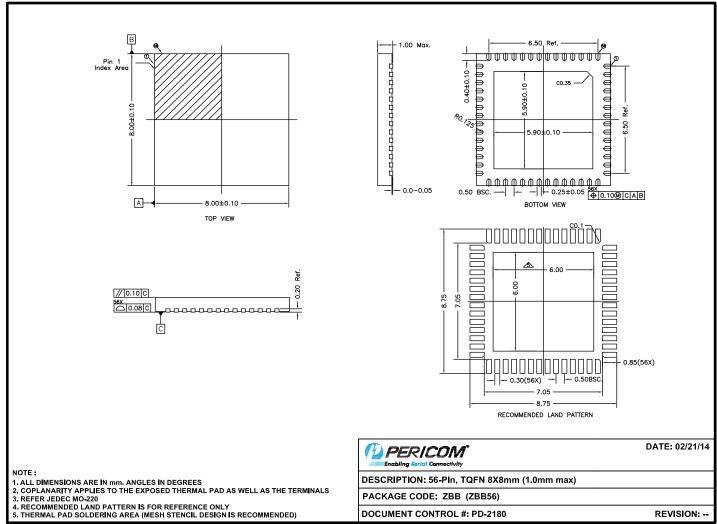
1st X: Assembly Code

2nd X: Fab Code





Packaging Mechanical: 56-TQFN (ZBB)



For latest package info.

 $please\ check: http://www.diodes.com/design/support/packaging/pericom-packaging/packaging-mechanicals-and-thermal-characteristics/packaging-mechanical-and-thermal-characteristics/packaging-mecha$

Ordering Information⁽¹⁻³⁾

Ordering Code	Package Code	Package Description	Operating Temperature
PI6LC48S25BZBBIEX	ZBB	56-Pin, 8x8mm, 1.0mm max (TQFN)	Industrial

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free. Thermal characteristics can be found on the company web site at www.diodes.com/design/support/packaging/
- 3. E = Pb-free and Green
- 4. X suffix = Tape/Reel





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